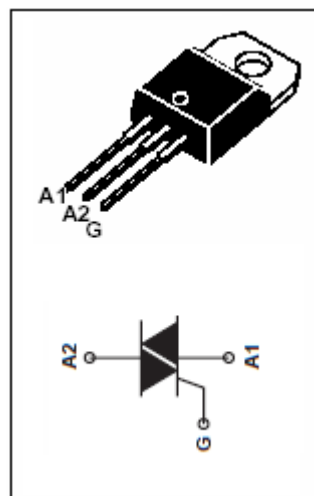


ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak reverse voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_j=105^{\circ}\text{C}$	12	A
I_{TSM}	Non-repetitive peak on-state current $t_p=20\text{ms}$	120	A
T_j	Operating junction temperature	110	℃
T_{stg}	Storage temperature	-45~150	℃
$R_{th(j-c)}$	Thermal resistance, junction to case	1.4	℃/W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	60	℃/W


ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER		CONDITIONS	MAX	UNIT
I_{RRM}	Repetitive peak reverse current		$V_R=V_{RRM}$, $V_R=V_{RRM}$, $T_j=110^{\circ}\text{C}$	0.01 0.5	mA
I_{DRM}	Repetitive peak off-state current		$V_D=V_{DRM}$, $V_D=V_{DRM}$, $T_j=110^{\circ}\text{C}$	0.01 0.5	mA
I_{GT}	Gate trigger current	I	$V_D=12\text{V}$; $R_L=30\ \Omega$	25	mA
		II		25	
		III		25	
		IV		50	
I_H	Holding current		$I_{GT}=0.5\text{A}$, Gate Open	25	mA
V_{GT}	Gate trigger voltage all quadrant		$V_D=12\text{V}$; $R_L=30\ \Omega$	1.3	V
V_{TM}	On-state voltage		$I_T=17\text{A}$; $t_p=380\ \mu\text{s}$	1.55	V